

UT54ACS541/UT54ACTS541

Features

- Three-state outputs drive bus lines or buffer memory address registers
- 1.2μ CMOS
 - Latchup immune
- High speed
- Low power consumption
- Single 5 volt supply
- Available QML Q or V processes
- Flexible package
 - 20-pin DIP
 - 20-lead flatpack
- UT54ACS541 - SMD 5962-96594
- UT54ACTS541 - SMD 5962-96595

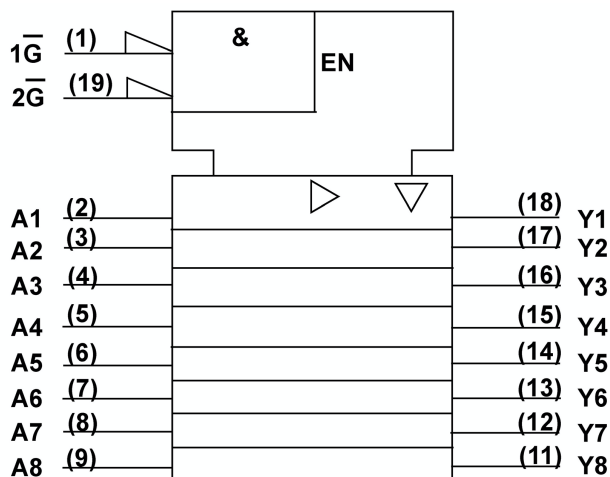
Description

The UT54ACS541 and the UT54ACTS541 are non-inverting octal buffers and line drivers which improve the performance and density of three-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. The devices are characterized over full military temperature range of -55°C to +125°C.

Function Table

Inputs			Output
$\overline{1G}$	$\overline{2G}$	A_n	Y_n
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

Logic Symbol

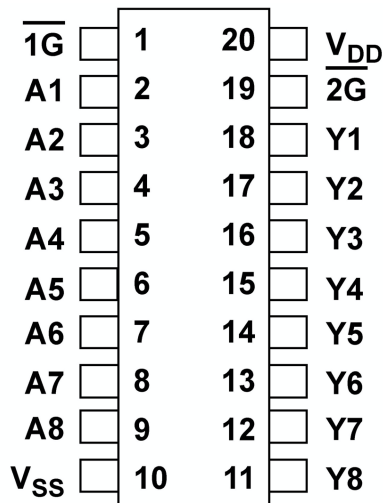


Note:

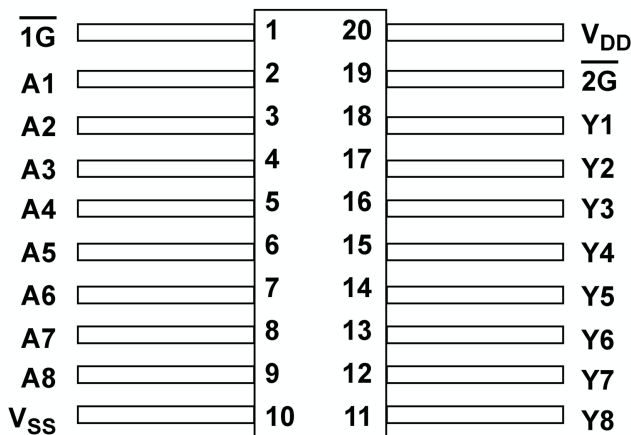
- 1) Logic symbol in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

UT54ACS541/UT54ACTS541

Pinouts

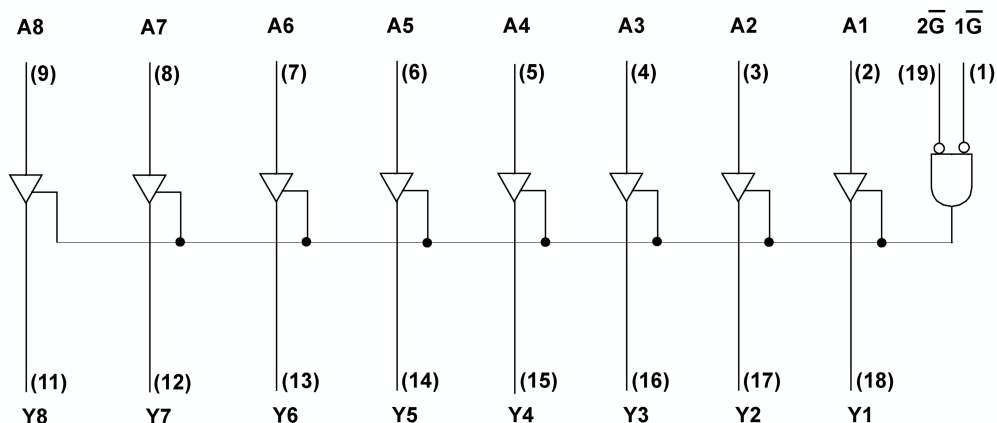


20-Pin DIP
Top View



20-Lead Flatpack
Top View

Logic Diagram



UT54ACS541/UT54ACTS541

Operational Environment¹

Parameter	Limit	Units
Total Dose	1.0E6	rads(Si)
SEU Threshold ²	80	MeV-cm ² /mg
SEL Threshold	120	MeV-cm ² /mg
Neutron Fluence	1.0E14	n/cm ²

Notes:

- 1) Logic will not latchup during radiation exposure within the limits defined in the table
- 2) Device storage elements are immune to SEU affects.

Absolute Maximum Ratings

Symbol	Parameter	Limit	Units
V _{DD}	Supply voltage	-0.3 to 7.0	V
V _{I/O}	Voltage any pin	-.3 to V _{DD} +.3	V
T _{STG}	Storage Temperature range	-65 to +150	°C
T _J	Maximum junction temperature	+175	°C
T _{LS}	Lead temperature (soldering 5 seconds)	+300	°C
θ _{JC}	Thermal resistance junction to case	20	°C/W
I _I	DC input current	±10	mA
P _D	Maximum power dissipation	1	W

Note:

- 1) Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other condition beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

V _{DD}	Supply voltage	4.5 to 5.5	V
V _{IN}	Input voltage any pin	0 to V _{DD}	V
T _C	Temperature range	-55 to + 125	°C

UT54ACS541/UT54ACTS541

DC Electrical Characteristics ⁷

($V_{DD} = 5.0V \pm 10\%$; $V_{SS} = 0V$ ⁶, $-55^{\circ}C < T_c < +125^{\circ}C$); unless otherwise noted, T_c is per the temperature range ordered.

Symbol	Parameter	Condition	MIN	MAX	Unit
V_{IL}	Low-level input voltage ¹ ACTS ACS			0.8 .3 V_{DD}	V
V_{IH}	High-level input voltage ¹ ACTS ACS		.5 V_{DD} .7 V_{DD}		V
I_{IN}	Input leakage current ACTS/ACS	$V_{IN} = V_{DD}$ or V_{SS}	-1	1	μA
V_{OL}	Low-level output voltage ³ ACTS ACS	$I_{OL} = 12.0mA$ $I_{OL} = 100\mu A$		0.40 0.25	V
V_{OH}	High-level output voltage ³ ACTS ACS	$I_{OH} = -12.0mA$ $I_{OH} = -100 \mu A$.7 V_{DD} $V_{DD} - 0.25$		V
I_{OZ}	Three-state output leakage current	$V_O = V_{DD}$ and V_{SS}	-30	30	μA
I_{OS}	Short-circuit output current ^{2, 4} ACTS/ACS	$V_O = V_{DD}$ and V_{SS}	-300	300	mA
I_{OL}	Output current ¹⁰ (Sink)	$V_{IN} = V_{DD}$ or V_{SS} $V_{OL} = 0.4V$	12		mA
I_{OH}	Output current ¹⁰ (Source)	$V_{IN} = V_{DD}$ or V_{SS} $V_{OH} = V_{DD} - 0.4V$	-12		mA
P_{total}	Power dissipation ^{2, 8, 9}	$C_L = 50pF$		2.1	mW/MHz
I_{DDQ}	Quiescent Supply Current	$V_{DD} = 5.5V$		10	μA
ΔI_{DDQ}	Quiescent Supply Current Delta ACTS	For input under test $V_{IN} = V_{DD} - 2.1V$ For all other inputs $V_{IN} = V_{DD}$ or V_{SS} $V_{DD} = 5.5V$		1.6	mA
C_{IN}	Input capacitance ⁵	$f = 1MHz @ 0V$		15	pF
C_{OUT}	Output capacitance ⁵	$f = 1MHz @ 0V$		15	pF

UT54ACS541/UT54ACTS541

Notes:

- 1) Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $V_{IH} = V_{IH(min)} + 20\%$, $- 0\%$; $V_{IL} = V_{IL(max)} + 0\%$, $- 50\%$, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to $V_{IH(min)}$ and $V_{IL(max)}$.
- 2) Supplied as a design limit but not guaranteed or tested.
- 3) Per MIL-PRF-38535, for current density $\leq 5.0E5$ amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765 pF/MHz
- 4) Not more than one output may be shorted at a time for maximum duration of one second.
- 5) Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and V_{SS} at frequency of 1MHz and signal amplitude of 50mV rms maximum.
- 6) Maximum allowable relative shift equals 50mV.
- 7) All ACS specifications are valid for radiation dose $\leq 1E6$ rads(Si), and all ACTS specifications are valid for radiation dose $\leq 5E5$ rads(Si).
- 8) Power does not include power contribution of any TTL output sink current.
- 9) Power dissipation specified per switching output.
- 10) This value is guaranteed based on characterization data, but not tested.

AC Electrical Characteristics ²

($V_{DD} = 5.0V \pm 10\%$; $V_{SS} = 0V$ ⁶, $-55^{\circ}C < T_C < +125^{\circ}C$); unless otherwise noted, T_C is per the temperature range ordered.

Symbol	Parameter	Minimum	Maximum	Unit
t_{PLH}	An to Yn	1	11	ns
t_{PHL}	An to Yn	1	14	ns
t_{PZL}	\bar{G} low to Yn active	2	14	ns
t_{PZH}	\bar{G} low to Yn active	2	15	ns
t_{PLZ}	\bar{G} high to Yn three-state	2	12	ns
t_{PHZ}	\bar{G} high to Yn three-state	2	13	ns

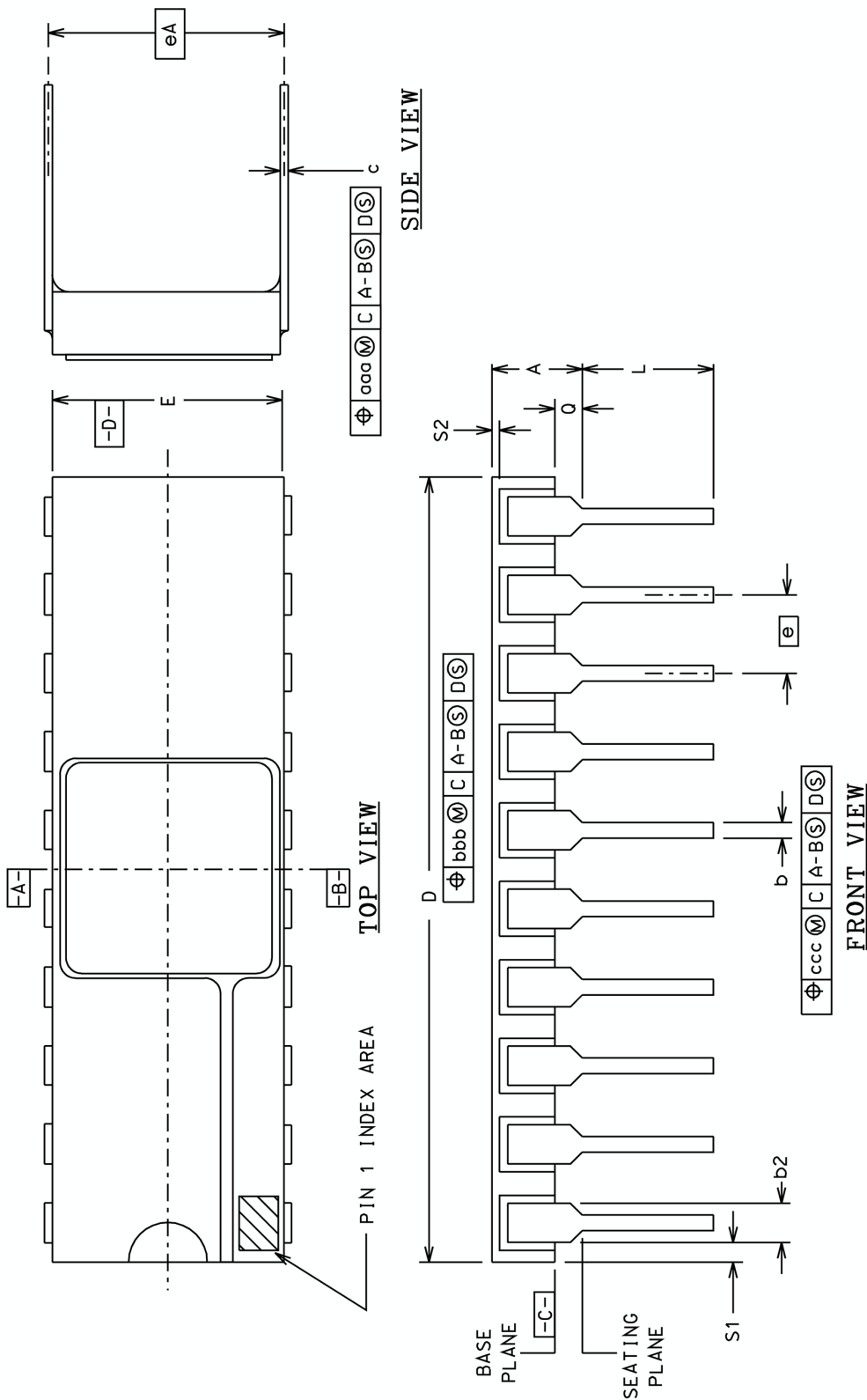
Notes:

- 1) Maximum allowable relative shift equals 50mV.
- 2) For the ACTS version, all specifications are valid for radiation dose $\leq 1E6$ rads(Si). For the ACTS version, all specifications are valid for radiation dose $\leq 5E5$ rads(Si).

UT54ACS541/UT54ACTS541

Packaging

Side-Brazed Packages

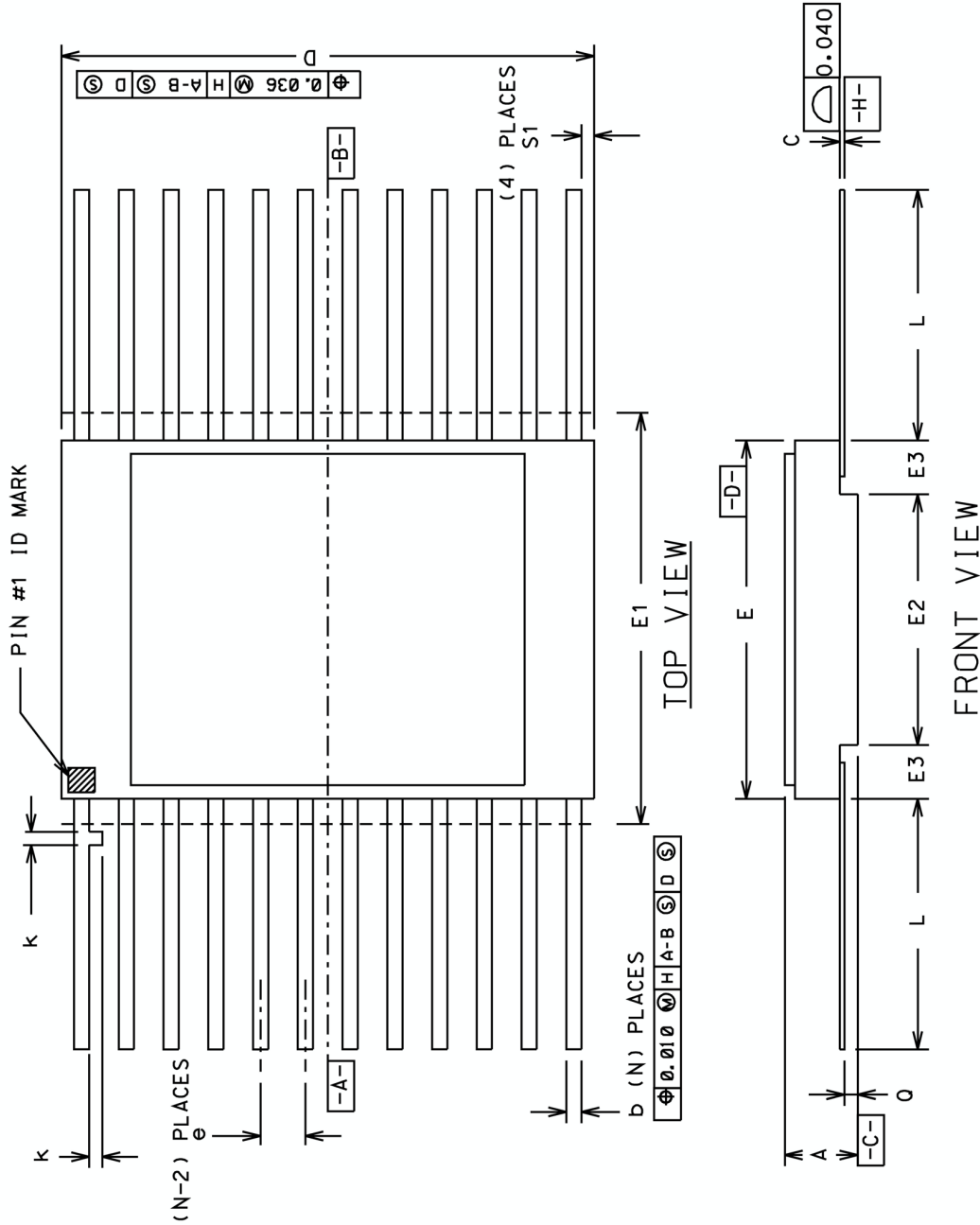


PKG CONF IG	LEAD COUNT	MIL-STD- 1835 DWG CONF C	DIMENSION SYMBOLS														
			A	b	b2	c	D	E	e	eA	L	Q	S1	S2	aaa	bbb	ccc
-01	14	D-1	0.200 ----- 0.014	0.026 0.014	0.065 0.045	0.018 0.008	0.785 ----- 0.840	0.310 0.220	0.100 BSC	0.300 BSC	0.200 0.125	0.060 0.015	----- 0.005	----- 0.005	0.015 -----	0.030 -----	0.010 -----
-02	16	D-2	0.200 ----- 0.014	0.026 0.014	0.065 0.045	0.018 0.008	0.840 ----- 1.060	0.310 0.220	0.100 BSC	0.300 BSC	0.200 0.125	0.060 0.015	----- 0.005	----- 0.005	0.015 -----	0.030 -----	0.010 -----
-03	20	D-8	0.200 ----- 0.014	0.026 0.014	0.065 0.045	0.018 0.008	1.060 ----- 1.060	0.310 0.220	0.100 BSC	0.300 BSC	0.200 0.125	0.070 0.015	----- 0.005	----- 0.005	0.015 -----	0.030 -----	0.010 -----

Octal Buffers & Line Drivers, Three-State Outputs

UT54ACS541/UT54ACTS541

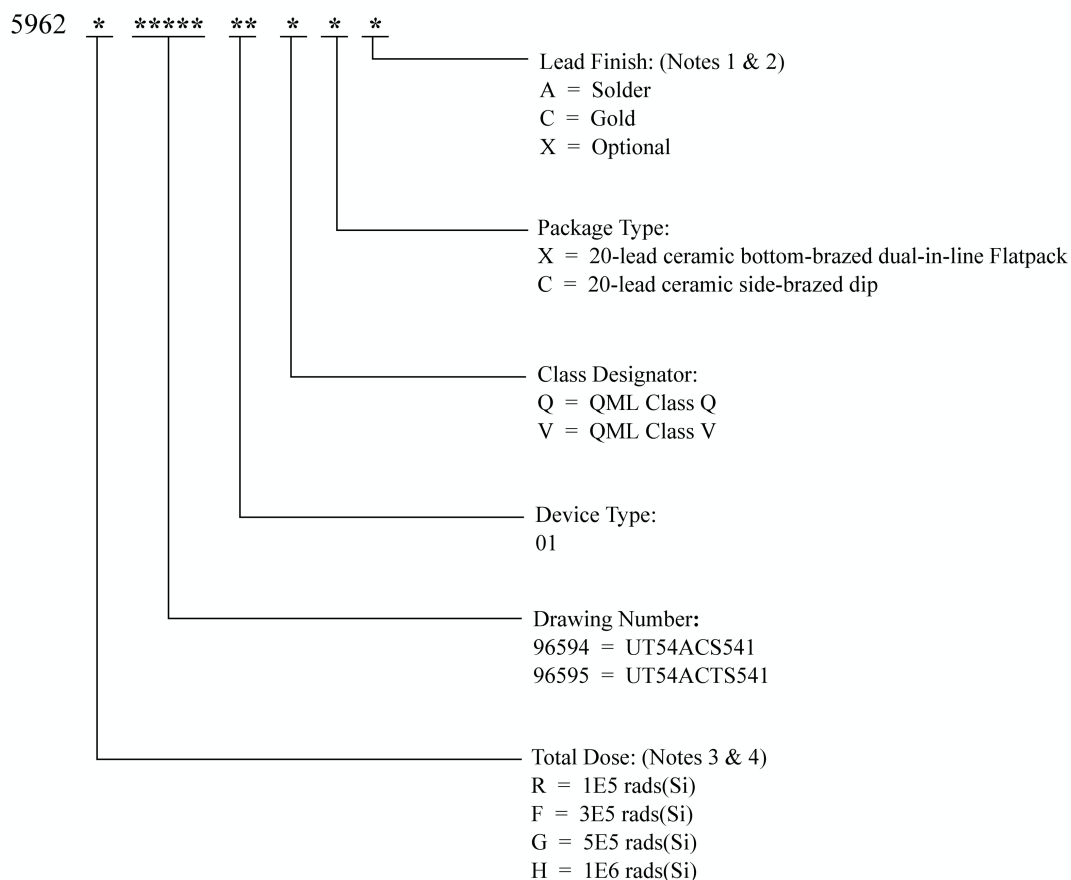
Flatpack Packages



PKG CONFIG	LEAD COUNT	MIL-STD 1835 DWG CONF B	DIMENSION SYMBOLS											
			A	b	c	D	E	E1	E2	E3	e	k	L	Q
-03	14	F-2A	0.115 0.045	0.022 0.015	0.009 0.004	0.390 -----	0.260 0.235	0.290 -----	0.130 -----	0.050 BSC	0.015 0.008	0.370 0.270	0.045 0.026	----- 0.005
-04	16	F-5A	0.115 0.045	0.022 0.015	0.009 0.004	0.440 -----	0.285 0.245	0.315 -----	0.130 -----	0.050 BSC	0.015 0.008	0.370 0.250	0.045 0.026	----- 0.005
-05	20	F-9A	0.115 0.045	0.022 0.015	0.009 0.004	0.540 -----	0.300 0.245	0.330 -----	0.130 0.030	0.050 BSC	0.015 0.008	0.370 0.250	0.045 0.026	----- 0.000

UT54ACS541/UT54ACTS541

UT54ACS541/UT54ACTS541: SMD



Notes:

- 1) Lead finish (A,C, or X) must be specified.
- 2) If an "X" is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
- 3) Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening. For prototype inquiries, contact factory.
- 4) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si) or 1E6 rads(Si) and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.

Octal Buffers & Line Drivers, Three-State Outputs

UT54ACS541/UT54ACTS541

Datasheet Definitions

	DEFINITION
Advanced Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is still in the development stage and the datasheet is subject to change . Specifications can be TBD and the part package and pinout are not final .
Preliminary Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is in the characterization stage and prototypes are available.
Datasheet	Product is in production and any changes to the product and services described herein will follow a formal customer notification process for form, fit or function changes.

The following United States (U.S.) Department of Commerce statement shall be applicable if these commodities, technology, or software are exported from the U.S.: These commodities, technology, or software were exported from the United States in accordance with the Export Administration Regulations. Diversion contrary to U.S. law is prohibited.

Cobham Colorado Springs Inc. d/b/a Cobham Advanced Electronic Solutions (CAES) reserves the right to make changes to any products and services described herein at any time without notice. Consult an authorized sales representative to verify that the information in this data sheet is current before using this product. The company does not assume any responsibility or liability arising out of the application or use of any product or service described herein, except as expressly agreed to in writing; nor does the purchase, lease, or use of a product or service convey a license under any patent rights, copyrights, trademark rights, or any other of the intellectual rights of the company or of third parties.